Handbook of Advanced Electronic and Photonic Materials and Devices

4

Ferroelectrics and Dielectrics

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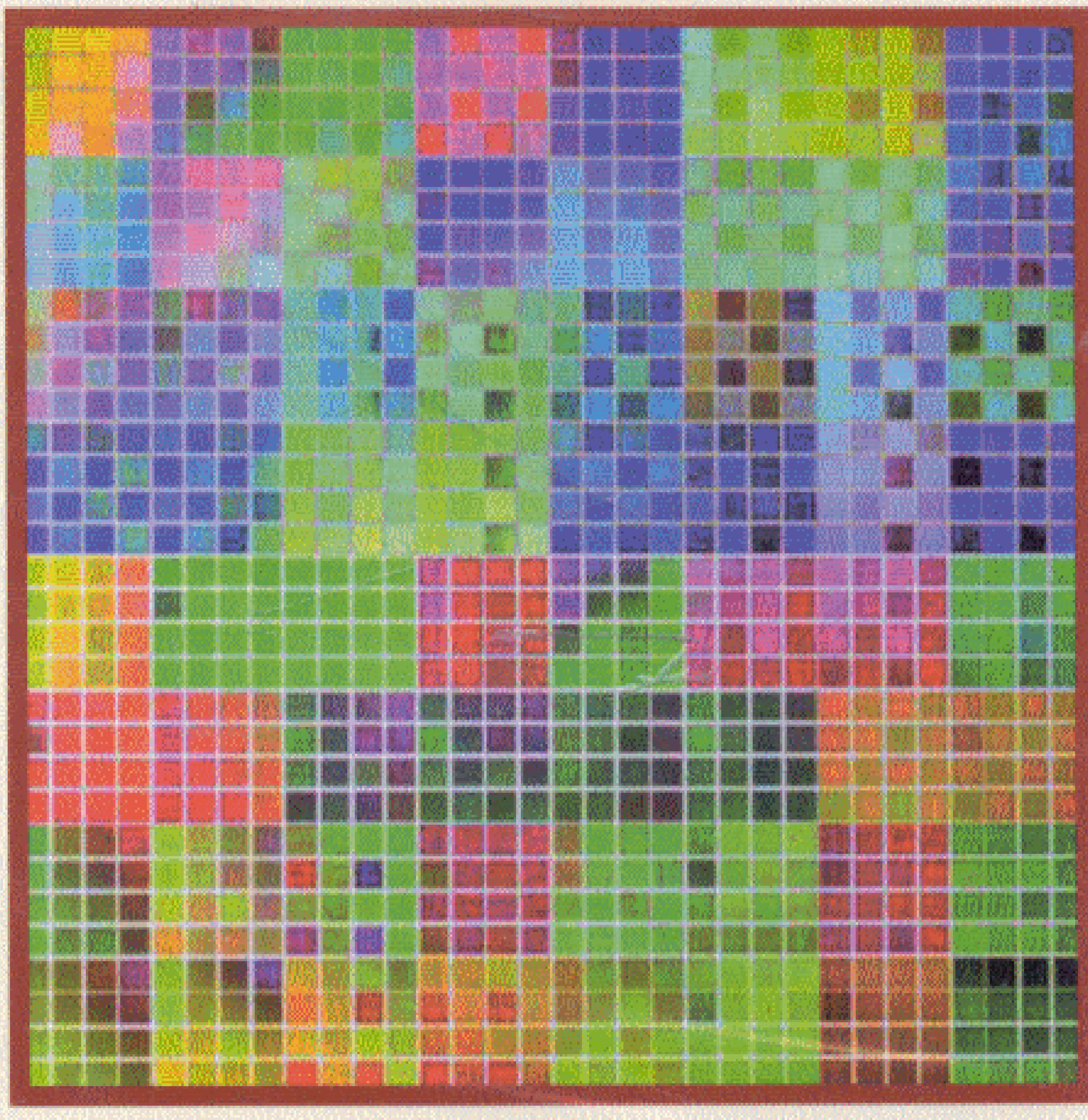

ACADEMIC PRESS

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